Supplementary Information

Structural, optical and charge generation properties of Chalcostibite and

Tetrahedrite copper antimony sulfide thin films prepared from metal

xanthates

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Fig. S1 Chemical structures of the used metal xanthates: (A) copper (I) O-2,2-dimethylpentan-3-yl dithiocarbonate, (B) antimony (III) O-propan-2-yl dithiocarbonate.



Fig. S2 Primary crystallite sizes of $CuSbS_2$ and $Cu_{12}Sb_4S_{13}$ thin films prepared at different temperatures estimated using Scherrer formula (corresponding XRD patterns are presented in Fig. 1).



Fig. S3 EDX spectra of Chalcostibite (A) and Tetrahedrite (B) layers annealed at 300 °C. The peaks assigned to chromium stem from a thin film of chromium sputtered on the samples to prevent electrical charging during SEM-EDX characterisation.



Fig. S4 Tauc plot to determine the indirect band gap of the prepared Chalcostibite film.



Fig. S5 XRD patterns of CuSbS₂ and Cu₁₂Sb₄S₁₃ thin films prepared on mesoporous TiO₂ layers. The main peaks in the patterns stemming from CuSbS₂ or Cu₁₂Sb₄S₁₃, respectively, are labelled are with their Miller indices (reference patterns: CuSbS₂ PDF 00-044-1417; Cu₁₂Sb₄S₁₃ PDF 01-088-0282). The peaks originating from the mesoporous TiO₂ film are also indicated in the graph.



Fig. S6 UV-VIS spectra of CuSbS₂ and Cu₁₂Sb₄S₁₃ thin films on mesoporous TiO₂ layers. The films were prepared using two different concentrations of the metal xanthates in the precursor solutions (0.18 and 0.36 M) and different numbers of coating and annealing steps. The optical density at 450 nm of the films prepared using a 0.36 M precursor solution is comparable to a 60 nm film of CuSbS₂ and Cu₁₂Sb₄S₁₃ on a planar glass substrate.